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(54) **BONDED BODY AND INSULATING CIRCUIT BOARD**

VERBUNDENER KÖRPER UND ISOLIERENDE LEITERPLATTE

CORPS LIÉ ET CARTE DE CIRCUIT IMPRIMÉ D'ISOLATION

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**Description**

TECHNICAL FIELD

5 **[0001]** The present invention relates to a bonded body having a structure in which an insulating resin member made of an insulating resin and a metal part are bonded, and an insulating circuit board.

**[0002]** Priority is claimed on Japanese Patent Application No. 2020-060041, filed March 30, 2020, and Japanese Patent Application No. 2020-161017, filed September 25, 2020,

10 BACKGROUND ART

**[0003]** Each of a power module, LED module, and thermoelectric module has a structure in which a power semiconductor element, an LED element, and a thermoelectric element are bonded to an insulating circuit board in which a circuit layer made of a conductive material is formed on one surface of an insulating layer. As the insulating layer, an insulating layer made of ceramics or an insulating resin has been proposed.

15 **[0004]** Here, as an insulating circuit board provided with an insulating resin layer, for example, a metal-based circuit board is proposed in Patent Document 1. In addition, a multilayer wiring board is proposed in Patent Document 2. Furthermore, an insulated circuit board comprising an insulating resin member is proposed in Patent Document 3.

**[0005]** In the metal-based circuit board described in Patent Document 1, an insulating resin layer is formed on a metal substrate, and a circuit layer having a circuit pattern is formed on this insulating resin layer. Here, the insulating resin layer is made of an epoxy resin that is a thermosetting resin, and the circuit layer is made of a copper foil.

20 **[0006]** This metal-based circuit board has a structure in which a semiconductor element is bonded onto the circuit layer, a heat sink is arranged on a surface of the metal substrate opposite to the insulating resin layer, and heat generated by the semiconductor element is transferred to the heat sink side to dissipate heat.

25 **[0007]** In addition, the multilayer wiring board described in Patent Document 2 is manufactured in such a manner that a surface roughness (Ra) of a metal foil is set to 0.2 μm or more, etching treatment is carried out on the metal foil adhered to a resin film, the etching treatment is further carried out on the metal foil to have a circuit pattern shape, thereby forming a wiring circuit layer, the wiring circuit layer formed on the surface of the resin film is embedded while applying pressure to a surface of a soft insulating sheet, an insulating circuit layer is transferred to the surface of the insulating sheet to obtain a plurality of insulating sheets, and the plurality of insulating sheets thus obtained are laminated and heat-cured all at one.

30 Furthermore, Patent Document 3 discloses a bonded body, as well as an insulating circuit board, having a structure in which an insulating resin member made of an insulating resin and a metal part made of a metal are bonded, wherein a bonded interface between the insulating resin member and the metal part has an uneven shape including a protrusion in which the metal part protrudes toward an insulating resin member side and a recess in which the metal part retracts from the insulating resin member side, and at least one of a kurtosis Rku of contour curve at the bonded interface of the metal part and a kurtosis Sku of contour surface at the bonded interface of the metal part is in a range of 2.75 or more and 6.00 or less.

[Citation List]

40 [Patent Documents]

**[0008]**

45 [Patent Document 1]  
Japanese Unexamined Patent Application, First Publication No. 2015-207666  
[Patent Document 2]  
Japanese Unexamined Patent Application, First Publication No. 2000-077850

50 SUMMARY OF INVENTION

Technical Problem

55 [Patent Document 3]

**[0009]** International Patent Application No. WO 2014/042201 A1

**[0010]** In an insulating circuit board having a structure in which a metal plate or the like is bonded to an insulating resin layer to form a circuit layer, it is important to ensure the adhesion between the insulating resin layer and the circuit layer

(metal plate) so that peeling of the circuit layer (metal plate) from the insulating resin layer does not occur during use.

**[0011]** Here, in the metal-based circuit board described in Patent Document 1, it was not considered to improve the adhesion between the insulating resin layer and the circuit layer, so that a risk for the occurrence of peeling of the circuit layer (metal plate) from the insulating resin layer during use has existed.

**[0012]** On the other hand, in the multilayer wiring board described in Patent Document 2, the object was to improve the adhesion between the insulating sheet and the wiring circuit layer by embedding the wiring circuit layer in the insulating sheet with the surface roughness (Ra) set to 0.2  $\mu\text{m}$  or more.

**[0013]** However, in a case where the surface roughness (Ra) of the metal plate (wiring circuit layer) is too large, electric charges are concentrated on a portion into which the metal plate surface intrudes, resulting in reduction in insulation properties (insulating withstand voltage) of the insulating resin layer. Therefore, there was a risk that the multilayer wiring board could not be used as an insulating circuit board.

**[0014]** The present invention has been made in view of the above-mentioned circumstances, and an objective of the present invention is to provide a bonded body that has excellent adhesion between an insulating resin member and a metal part, has excellent insulation properties in the insulating resin member and can be stably used, and an insulating circuit board.

#### Solution to Problem

**[0015]** In order to solve the above-mentioned problems, a bonded body of the present invention has a structure in which an insulating resin member made of an insulating resin and a metal part made of a metal are bonded, and in the bonded body, a bonded interface between the insulating resin member and the metal part has an uneven shape including a protrusion in which the metal part protrudes toward an insulating resin member side and a recess in which the metal part retracts from the insulating resin member side, at least one of a kurtosis Rku of contour curve at the bonded interface of the metal part and a kurtosis Sku of contour surface at the bonded interface of the metal part is in a range of 2.75 or more and 6.00 or less, and an overhang rate that indicates a length ratio of regions overlapping in a lamination direction in a direction along the bonded interface is 7% or more.

**[0016]** According to the bonded body having this configuration, since the bonded interface between the insulating resin member and the metal part has an uneven shape including a protrusion in which the metal part protrudes toward an insulating resin member side and a recess in which the metal part retracts from the insulating resin member side, and at least one of a kurtosis Rku of contour curve at the bonded interface of the metal part and a kurtosis Sku of contour surface at the bonded interface of the metal part is in a range of 2.75 or more and 6.00 or less, a tip of the protrusion is not sharpened more than necessary, and the insulation properties (insulating withstand voltage) of the insulating resin member can be sufficiently ensured.

**[0017]** Furthermore, since the overhang rate indicating the length ratio of regions overlapping in a lamination direction in a direction along the bonded interface is 7% or more, the metal part and the insulating resin member are sufficiently engaged, and the adhesion between the insulating resin member and the metal part can be improved.

**[0018]** Here, in the bonded body of the present invention, at least one of the root mean square deviation Rq of contour curve at the bonded interface of the metal part and the root mean square deviation Sq of contour surface at the bonded interface of the metal part is preferably in a range of 0.20  $\mu\text{m}$  or more and 0.90  $\mu\text{m}$  or less.

**[0019]** In this case, since at least one of the root mean square deviation Rq of contour curve at the bonded interface of the metal part and the root mean square deviation Sq of contour surface at the bonded interface of the metal part is in a range of 0.20  $\mu\text{m}$  or more and 0.90  $\mu\text{m}$  or less, it is possible to suppress the generation of electric field concentration at the tip of the protrusion, surely ensure the insulation properties, and improve the adhesion between the insulating resin member and the metal part.

**[0020]** An insulating circuit board of the present invention includes an insulating resin layer, and a circuit layer in which a metal plate is bonded to one surface of the insulating resin layer, and in the insulating circuit board, a bonded interface between the insulating resin layer and the circuit layer has an uneven shape including a protrusion in which the circuit layer protrudes toward an insulating resin layer side and a recess in which the circuit layer retracts from the insulating resin layer side, at least one of a kurtosis Rku of contour curve at the bonded interface of the circuit layer and a kurtosis Sku of contour surface at the bonded interface of the circuit layer is in a range of 2.75 or more and 6.00 or less, and an overhang rate that indicates a length ratio of regions overlapping in a lamination direction in a direction along the bonded interface is 7% or more.

**[0021]** According to the insulating circuit board having this configuration, since the bonded interface between the insulating resin layer and the circuit layer has an uneven shape including a protrusion in which the circuit layer protrudes toward an insulating resin layer side and a recess in which the circuit layer retracts from the insulating resin layer side, and at least one of a kurtosis Rku of contour curve at the bonded interface of the circuit layer and a kurtosis Sku of contour surface at the bonded interface of the circuit layer is in a range of 2.75 or more and 6.00 or less, the tip of the protrusion is not sharpened more than necessary, and the insulation properties (insulating withstand voltage) of the insulating resin portion

layer can be sufficiently ensured.

**[0022]** Furthermore, since the overhang rate indicating the length ratio of regions overlapping in a lamination direction in a direction along the bonded interface is 7% or more, the circuit layer and the insulating resin layer are sufficiently engaged, and the adhesion between the circuit layer and the insulating resin layer can be improved.

**[0023]** Here, in the insulating circuit board of the present invention, at least one of the root mean square deviation Rq of contour curve at the bonded interface of the circuit layer and the root mean square deviation Sq of contour surface at the bonded interface of the circuit layer is preferably in a range of 0.20  $\mu\text{m}$  or more and 0.90  $\mu\text{m}$  or less.

**[0024]** In this case, since at least one of the root mean square deviation Rq of contour curve at the bonded interface of the circuit layer and the root mean square deviation Sq of contour surface at the bonded interface of the circuit layer is in a range of 0.20  $\mu\text{m}$  or more and 0.90  $\mu\text{m}$  or less, it is possible to suppress the generation of electric field concentration at the tip of the protrusion, surely ensure the insulation properties, and surely improve the adhesion between the insulating resin layer and the circuit layer.

#### Advantageous Effects of Invention

**[0025]** According to the present invention, it is possible to provide the bonded body that has exceptional adhesion between the insulating resin member and the metal part, has exceptional insulation properties in the insulating resin member, and can be stably used, and the insulating circuit board.

#### BRIEF DESCRIPTION OF DRAWINGS

##### **[0026]**

Fig. 1 is a schematic explanatory diagram of a power module provided with an insulating circuit board according to an embodiment of the present invention.

Fig. 2 is a flow chart showing a method for manufacturing an insulating circuit board according to an embodiment of the present invention.

Fig. 3 shows cross-sectional observation photographs of a metal plate (metal substrate) before and after a surface roughening step S01 in the method for manufacturing an insulating circuit board according to the embodiment of the present invention. Fig. 3(a) is a photograph before the surface roughening step S01 is carried out, and Fig. 3(b) is a photograph after the surface roughening step S01 is carried out.

Fig. 4 is a schematic explanatory diagram of the method for manufacturing an insulating circuit board shown in Fig. 2.

Fig. 5 is an explanatory diagram showing a measurement example of an overhang rate in Example.

Fig. 6 is a schematic explanatory diagram of a test device for evaluating insulation properties (insulating withstand voltage) of the insulating circuit board in Example.

#### DESCRIPTION OF EMBODIMENTS

**[0027]** Hereinafter, embodiments of the present invention will be described with reference to the accompanying drawings.

**[0028]** The bonded body according to the present embodiment includes an insulating circuit board 10 configured by bonding an insulating resin layer 12 that is an insulating resin member to a metal plate 23 (circuit layer 13) that is a metal part and a metal substrate 11.

**[0029]** Fig. 1 shows the insulating circuit board 10 according to the embodiment of the present invention and a power module 1 using the insulating circuit board 10.

**[0030]** The power module 1 shown in Fig. 1 is provided with the insulating circuit board 10, a semiconductor element 3 that is bonded, through a first solder layer 2, to one surface (upper surface shown in Fig. 1) of the insulating circuit board 10, and a heat sink 31 that is bonded, through a solder layer 32, to the other side (lower side shown in Fig. 1) of the insulating circuit board 10.

**[0031]** The semiconductor element 3 is made of a semiconductor material such as Si. The first solder layer 2 for bonding the insulating circuit board 10 and the semiconductor element 3 is made of, for example, a Sn-Ag-based solder material, a Sn-Cu-based solder material, a Sn-In-based solder material, or a Sn-Ag-Cu-based solder material (so-called lead-free solder material).

**[0032]** The heat sink 31 dissipates heat on the insulating circuit board 10 side. The heat sink 31 is made of copper or a copper alloy, aluminum or an aluminum alloy, or the like, which have good thermal conductivity. In the present embodiment, the heat sink is a heat radiation plate made of oxygen-free copper. A thickness of the heat sink 31 is set in a range of 3 mm or more and 10 mm or less.

**[0033]** Here, the insulating circuit board 10 and the heat sink 31 are bonded through the solder layer 32. This solder layer

32 can have the same configuration as the above-mentioned solder layer 2.

[0034] As shown in Fig. 1, the insulating circuit board 10 of the present embodiment includes the metal substrate 11, the insulating resin layer 12 formed on one surface (upper surface shown in Fig. 1) of the metal substrate 11, and the circuit layer 13 formed on one surface (upper surface shown in Fig. 1) of the insulating resin layer 12.

[0035] The metal substrate 11 has an action of improving a heat dissipating feature by spreading heat generated in the semiconductor element 3 mounted on the insulating circuit board 10 in a plane direction. Therefore, the metal substrate 11 is made of a metal having excellent thermal conductivity, for example, copper or a copper alloy, or aluminum or an aluminum alloy. In the present embodiment, the metal substrate 11 is made of a rolled plate composed of oxygen-free copper. A thickness of the metal substrate 11 is set in a range of 0.05 mm or more and 3 mm or less and is set to 2.0 mm in the present embodiment.

[0036] The insulating resin layer 12 prevents electrical connection between the circuit layer 13 and the metal substrate 11 and is made of a thermosetting resin with insulation properties.

[0037] In the present embodiment, a thermosetting resin containing a filler is used to ensure the strength of the insulating resin layer 12 and to ensure the thermal conductivity. Here, as the filler, for example, alumina, boron nitride, aluminum nitride, or the like can be used. In addition, as the thermosetting resin, an epoxy resin, a polyimide resin, or the like can be used. In the present embodiment, the insulating resin layer 12 is made of an epoxy resin containing alumina as a filler. A thickness of the insulating resin layer 12 is in a range of 20  $\mu\text{m}$  or more and 250  $\mu\text{m}$  or less and is 150  $\mu\text{m}$  in the present embodiment.

[0038] As shown in Fig. 4, the circuit layer 13 is formed such that the metal plate 23 made of a metal having excellent conductivity is bonded to one surface (upper surface shown in Fig. 4) of the insulating resin layer 12. As the metal plate 23, a rolled plate made of a material such as copper or a copper alloy, aluminum or an aluminum alloy can be used. In the present embodiment, a rolled plate made of oxygen-free copper is used as the metal plate 23 constituting the circuit layer 13.

[0039] In the circuit layer 13, a circuit pattern is formed, and one surface (upper surface shown in Fig. 1) thereof is a mounting surface on which the semiconductor element 3 is mounted. Here, a thickness of the circuit layer 13 (metal plate 23) is set in a range of 0.3 mm or more and 3 mm or less and is set to 0.5 mm in the present embodiment.

[0040] In the insulating circuit board 10 of the present embodiment, a bonded interface between the insulating resin layer 12 and the circuit layer 13 (metal substrate 11) has an uneven shape including a protrusion 18 in which the circuit layer 13 (metal substrate 11) protrudes toward the insulating resin layer 12 side and a recess 19 in which the circuit layer 13 (metal substrate 11) retracts from the insulating resin layer 12 side.

[0041] That is, in the present embodiment, the circuit layer 13 (metal substrate 11) intrudes into the insulating resin layer 12.

[0042] Here, in the present embodiment, at least one of a kurtosis  $R_{ku}$  of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and a kurtosis  $S_{ku}$  of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is in a range of 2.75 or more and 6.00 or less.

[0043] In addition, an overhang rate that indicates a length ratio of regions overlapping in a lamination direction in a direction along the bonded interface is 7% or more.

[0044] In the present embodiment, at least one of the root mean square deviation  $R_q$  of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the root mean square deviation  $S_q$  of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is preferably in a range of 0.20  $\mu\text{m}$  or more and 0.90  $\mu\text{m}$  or less.

[0045] Hereinafter, regarding the insulating circuit board 10 of the present embodiment, the reason why the kurtosis of assessed profile  $R_{ku}$  at the bonded interface of the circuit layer 13 (metal substrate 11), the kurtosis of scale-limited surface  $S_{ku}$  at the bonded interface of the circuit layer 13 (metal substrate 11), the overhang rate that indicates a length ratio of regions overlapping in the lamination direction in the direction along the bonded interface, the root mean square deviation of assessed profile  $R_q$  at the bonded interface of the circuit layer 13 (metal substrate 11), and the root mean square deviation of scale-limited surface  $S_q$  at the bonded interface of the circuit layer 13 (metal substrate 11) are defined as mentioned above will be described.

(Kurtosis of Assessed Profile  $R_{ku}$  and Kurtosis of Scale-limited Surface  $S_{ku}$  at Bonded Interface)

[0046] The kurtosis of assessed profile  $R_{ku}$  is a parameter defined in JIS B 0601:2001, the kurtosis of scale-limited surface  $S_{ku}$  is a parameter defined in JIS B 0681-2:2018, and each of the parameters is obtained by evaluating kurtosis that is a measure of surface sharpness.

[0047] The kurtosis of assessed profile  $R_{ku}$  is  $R_{ku} = 3$  in the shape of the normal distribution,  $R_{ku} > 3$  in a case where the height distribution is sharper than the normal distribution, and  $R_{ku} < 3$  in a case where the height distribution is crushed as compared with the normal distribution.

[0048] In addition, the Kurtosis of scale-limited surface  $S_{ku}$  is a parameter in which the kurtosis of assessed profile  $R_{ku}$  extends to three dimensions.

**[0049]** Here, in a case where both the kurtosis of assessed profile Rku and the kurtosis of scale-limited surface Sku at the bonded interface of the circuit layer 13 (metal substrate 11) are less than 2.75, the surface of the circuit layer 13 (the tip of the protrusion 18) is shaped in a crushed state, so that the circuit layer 13 (metal substrate 11) may not sufficiently intrude into the insulating resin layer 12 side, and the adhesion between the insulating resin layer 12 and the circuit layer 13 (metal substrate 11) may not be improved. On the other hand, in a case where both the kurtosis of assessed profile Rku and the kurtosis of scale-limited surface Sku at the bonded interface of the circuit layer 13 (metal substrate 11) are more than 6.00, the surface of the circuit layer 13 (the tip of the protrusion 18) is sharper than necessary, so that electric field concentration is generated at the tip of the protrusion 18, and insulation properties (insulating withstand voltage) of the insulating resin layer 12 may not be ensured.

**[0050]** Therefore, in the present embodiment, at least one of the kurtosis Rku of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and a kurtosis Sku of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is set to be in the range of 2.75 or more and 6.00 or less.

**[0051]** At least one of the kurtosis Rku of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the kurtosis Sku of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is preferably 2.75 or more, and still more preferably 3.00 or more. On the other hand, at least one of the kurtosis Rku of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the kurtosis Sku of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is preferably 6.00 or less, and still more preferably 3.75 or less.

(Overhang Rate)

**[0052]** The overhang rate in the present embodiment is obtained in such a manner that the cross-sectional shape of the bonded interface is image-analyzed with image processing software, regions overlapping in a lamination direction (height direction: Y direction) in a direction along the bonded interface (horizontal direction: X direction) with respect to the obtained cross-sectional curve are defined as overhang portions, which is defined as a ratio of lengths of the overhang portions in the X direction to all of the length of the obtained cross-sectional curve in the X direction.

**[0053]** In a case of counting the lengths of the overhang portions in the X direction, for example, it is counted as 0 in a case where there is no overhang portion in the Y direction, it is counted as 1 in a case where there is one overhang portion in the Y direction, and it is counted as 2 in a case where there are two overhang portions in the Y direction, and it is counted as the plural number in a case where there are a plurality of the overhang portions. Therefore, the overhang rate may be 100% or more.

**[0054]** Here, in a case where the overhang rate that indicates the length ratio of regions overlapping in the lamination direction in the direction along the bonded interface is less than 7%, the circuit layer 13 (metal substrate 11) and the insulating resin layer 12 are not sufficiently engaged, and the adhesion between the insulating resin layer 12 and the circuit layer 13 (metal substrate 11) may not be improved.

**[0055]** Therefore, in the present embodiment, the overhang rate that indicates the length ratio of regions overlapping in the lamination direction in the direction along the bonded interface is defined as 7% or more.

**[0056]** The above-mentioned overhang rate is preferably 7% or more, and still more preferably 15% or more. On the other hand, the overhang rate is not particularly limited, but is preferably 100% or less.

(Root Mean Square Deviation of Assessed Profile Rq and Root Mean Square Deviation of Scale-limited Surface Sq at Bonded Interface)

**[0057]** The root mean square deviation of assessed profile Rq is a parameter specified in JIS B 0601: 2001, and the root mean square deviation of scale-limited surface Sq is a parameter specified in JIS B 0681-2:2018, each of which means the standard deviation of the surface roughness.

**[0058]** In the insulating circuit board 10 of the present embodiment, the circuit layer 13 (metal substrate 11) sufficiently intrudes into the insulating resin layer 12 side by setting at least one of the root mean square deviation Rq of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the root mean square deviation Sq of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) to 0.20  $\mu\text{m}$  or more, so that the adhesion between the insulating resin layer 12 and the circuit layer 13 (metal substrate 11) can be surely improved. On the other hand, the generation of electric field concentration at the tip of the protrusion 18, which is formed by the circuit layer 13 (metal substrate 11) intruding inside the insulating resin layer 12, can be suppressed by setting at least one of the root mean square deviation Rq of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the root mean square deviation Sq of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) to 0.90  $\mu\text{m}$  or less, so that the insulation properties of the insulating resin layer 12 can be surely ensured.

**[0059]** Therefore, in the insulating circuit board 10 of the present embodiment, at least one of the root mean square deviation Rq of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the root mean square deviation Sq of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is preferably in the range

of 0.20  $\mu\text{m}$  or more and 0.90  $\mu\text{m}$  or less.

**[0060]** At least one of the root mean square deviation  $R_q$  of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the root mean square deviation  $S_q$  of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is preferably 0.20  $\mu\text{m}$  or more, and still more preferably 0.30  $\mu\text{m}$  or more. By contrast, at least one of the root mean square deviation  $R_q$  of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the root mean square deviation  $S_q$  of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is preferably 0.90  $\mu\text{m}$  or less, and still more preferably 0.80  $\mu\text{m}$  or less.

**[0061]** Next, a method for manufacturing the insulating circuit board 10 according to the present embodiment will be described with reference to Figs. 2 to 4.

(Surface Roughening Step S01)

**[0062]** First, a roughened plating layer 23a is formed on a bonding surface between the metal plate 23 serving as the circuit layer 13 and the insulating resin layer 12, and a roughened plating layer 11a is formed on a bonding surface between the metal substrate 11 and the insulating resin layer 12. As a result, uneven portions are formed on the bonding surface between the metal plate 23 serving as the circuit layer 13 and the insulating resin layer 12 and the bonding surface between the metal substrate 11 and the insulating resin layer 12. The roughened plating layers 23a and 11a are formed as follows.

**[0063]** Electrolytic plating treatment is carried out on the bonding surfaces between the metal plate 23 and the metal substrate 11. In the present embodiment, it is preferable to use an electrolytic solution consisting of an aqueous solution that is obtained by adding 3,3'-dithiobis(1-propane sulfonic acid)<sub>2</sub> sodium into a copper sulfate bath containing copper sulfate ( $\text{CuSO}_4$ ) and sulfuric acid ( $\text{H}_2\text{SO}_4$ ) as main components, as an electrolytic plating solution. A temperature of the plating bath is preferably in a range of, for example, 25°C or higher and 35°C or lower.

**[0064]** As the electrolytic plating treatment, a periodic reverse (PR) pulse plating treatment is used. This PR pulse plating treatment is a method of performing electrolytic plating by energization while periodically reversing a direction of electric current. For example, positive electrolysis (anodic electrolysis in which the metal plate 23 and the metal substrate 11 serve as an anode) of 1 A/dm<sup>2</sup> or more and 30 A/dm<sup>2</sup> or less is set to 1 ms or more and 1000 ms or less, and negative electrolysis (cathode electrolysis in which the metal plate 23 and the metal substrate 11 serve as a cathode) of 1 A/dm<sup>2</sup> or more and 30 A/dm<sup>2</sup> or less is set to 1 ms or more and 1000 ms or less, which is repeated.

As a result, the melting of the surfaces of the metal plate 23 and the metal substrate 11 and the precipitation of copper are repeatedly carried out, thereby forming the roughened plating layers 23a and 11a.

**[0065]** Here, it is possible to adjust the kurtosis of assessed profile  $R_{ku}$ , the kurtosis of scale-limited surface  $S_{ku}$ , the overhang rate, the root mean square deviation of assessed profile  $R_q$ , and the root mean square deviation of scale-limited surface  $S_q$  at the bonding surface between the metal plate 23 and the metal substrate 11 based on surface properties of the metal plate 23 and the metal substrate 11 before forming the roughened plating layers 23a and 11a, and various plating conditions (pulse application time, pulse waveform (ratio of precipitation amount/melting amount), and pulse frequency).

**[0066]** For example, in a case where the pulse application time is lengthened, the kurtosis of assessed profile  $R_{ku}$  and the kurtosis of scale-limited surface  $S_{ku}$  each are close to 3, the overhang rate increases, and the root mean square deviation of assessed profile  $R_q$  and the root mean square deviation of scale-limited surface  $S_q$  increase.

**[0067]** In addition, in a case where, as a pulse waveform, the ratio of precipitation amount/melting amount is increased, the kurtosis of assessed profile  $R_{ku}$  and the kurtosis of scale-limited surface  $S_{ku}$  each increase, the overhang rate decreases, and the root mean square deviation of assessed profile  $R_q$  and the root mean square deviation of scale-limited surface  $S_q$  decrease.

**[0068]** Furthermore, in a case where the pulse frequency is increased, the kurtosis of assessed profile  $R_{ku}$  and the kurtosis of scale-limited surface  $S_{ku}$  each are close to 3, the overhang rate decreases, and the root mean square deviation of assessed profile  $R_q$  and the root mean square deviation of scale-limited surface  $S_q$  decrease.

**[0069]** Here, Fig. 3(a) shows a cross-sectional photograph of the metal plate 23 (metal substrate 11) before the surface roughening step S01 is carried out, and Fig. 3(b) shows a cross-sectional photograph of the metal plate 23 (metal substrate 11) after the surface roughening step S01 is carried out.

**[0070]** It is confirmed that the uneven portion is formed on the bonding surface of the metal plate 23 (metal substrate 11) by carrying out the surface roughening step S01 of the present embodiment, and the overhang portion is formed.

(Laminating Step S02)

**[0071]** Next, a resin composition 22 containing alumina as a filler, an epoxy resin as a thermosetting resin, and a curing agent is arranged on one surface (upper surface shown in Fig. 4) of the metal substrate 11. In the present embodiment, the resin composition 22 is formed in a sheet shape.

**[0072]** The metal plate 23 serving as the circuit layer 13 is arranged on one surface (upper surface shown in Fig. 4) of the resin composition 22.

(Thermocompression Bonding Step S03)

5 **[0073]** Next, the metal substrate 11, the resin composition 22, and the metal plate 23, which have been laminated, are pressurized and heated in a lamination direction, the resin composition 22 is cured to form the insulating resin layer 12, thereby bonding the metal substrate 11 and the insulating resin layer 12 to each other and bonding the insulating resin layer 12 and the metal plate 23 to each other.

10 **[0074]** In this thermocompression bonding step S03, conditions in which a heating temperature is within a range of 150°C or higher and 400°C or lower, a holding time at the heating temperature is within a range of 30 minutes or longer and 90 minutes or shorter, and a pressurizing pressure in the lamination direction is in a range of 1 MPa or more and 100 MPa or less are preferably employed.

(Circuit Pattern Forming Step S04)

15 **[0075]** Next, the metal plate 23 bonded to the insulating resin layer 12 is subjected to etching treatment to form a circuit pattern, thereby forming the circuit layer 13.

**[0076]** As described above, the insulating circuit board 10 according to the present embodiment is manufactured.

(Heat Sink Bonding Step S05)

20 **[0077]** Next, the heat sink 31 is bonded to the other surface of the metal substrate 11 of the insulating circuit board 10. In the present embodiment, the metal substrate 11 and the heat sink 31 are bonded through a solder material.

(Semiconductor Element-Bonding Step S06)

25 **[0078]** The semiconductor element 3 is bonded to the circuit layer 13 of the insulating circuit board 10. In the present embodiment, the circuit layer 13 and the semiconductor element 3 are bonded through a solder material.

**[0079]** The power module 1 shown in Fig. 1 is manufactured by the above-mentioned steps.

30 **[0080]** According to the insulating circuit board 10 (bonded body) of the present embodiment, since the bonded interface between the insulating resin layer 12 and the circuit layer 13 (metal substrate 11) has an uneven shape including the protrusion 18 in which the circuit layer 13 (metal substrate 11) protrudes toward the insulating resin layer 12 side and the recess 19 in which the circuit layer 13 (metal substrate 11) retracts from the insulating resin layer 12 side, and at least one of the kurtosis Rku of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the kurtosis Sku of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is set to 2.75 or more, the circuit layer 13 (metal substrate 11) sufficiently intrudes into the insulating resin layer 12 side, so that the adhesion between the insulating resin layer 12 and the circuit layer 13 (metal substrate 11) can be improved. In addition, since at least one of the kurtosis Rku of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the kurtosis Sku of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is set to 6.00 or less, the tip of the protrusion 18 is not sharpened more than necessary, and the insulation properties (insulating withstand voltage) of the insulating resin portion layer can be sufficiently ensured.

40 **[0081]** Furthermore, since the overhang rate indicating the length ratio of regions overlapping in the lamination direction in the direction along the bonded interface is 7% or more, the circuit layer 13 (metal substrate 11) and the insulating resin layer 12 are sufficiently engaged, and the adhesion between the circuit layer 13 (metal substrate 11) and the insulating resin layer 12 can be improved.

45 **[0082]** Here, in the insulating circuit board 10 (bonded body) of the present embodiment, in a case where at least one of the root mean square deviation Rq of contour curve at the bonded interface of the circuit layer 13 (metal substrate 11) and the root mean square deviation Sq of contour surface at the bonded interface of the circuit layer 13 (metal substrate 11) is in the range of 0.20 μm or more and 0.90 μm or less, it is possible to suppress the generation of electric field concentration at the tip of the protrusion 18, surely ensure the insulation properties in the insulating resin layer 12, and surely improve the adhesion between the circuit layer 13 (metal substrate 11) and the insulating resin layer 12.

50 **[0083]** In the present embodiment, the insulating circuit board is manufactured by the method for manufacturing the insulating circuit board shown in Figs. 2 to 4, but the present invention is not limited thereto.

55 **[0084]** In the present embodiment, the metal plate for forming the metal substrate and the circuit layer is described as being composed of oxygen-free copper, but the metal plate is not limited thereto, and may be made of another metal composed of copper or a copper alloy or may be made of another metal such as aluminum or an aluminum alloy. Furthermore, a structure in which a plurality of metals are laminated may be adopted.

**[0085]** Furthermore, in the present embodiment, the configuration of the power module in which the semiconductor element is mounted on the insulating circuit board is described, but the present invention is not limited thereto. For example, a configuration of an LED module in which a LED element is mounted on the circuit layer of the insulating circuit

board may be adopted, or a configuration of a thermoelectric module in which a thermoelectric element is mounted on the circuit layer of the insulating circuit board may be adopted.

## EXAMPLES

5 [0086] The results of a confirmation experiment conducted to confirm the effect of the present invention will be described below.

[0087] A metal substrate (40 mm × 40 mm × thickness of 2 mm) formed of a rolled plate made of oxygen-free copper and a metal plate serving as the circuit layer (40 mm × 40 mm × thickness of 0.5 mm) were prepared, and a roughened plating layer was formed on a bonding surface between these metal substrate and insulating resin layer of the metal plate by the PR pulse electrolysis method described in the above-mentioned embodiment.

10 [0088] Then, a sheet material (40 mm × 40 mm × thickness of 0.15 mm) composed of a resin composition containing an epoxy resin containing Al<sub>2</sub>O<sub>3</sub> as a filler was disposed on a surface on which the roughened plating layer of the metal substrate was formed.

15 [0089] In addition, the metal plate serving as the circuit layer was laminated on one surface of the sheet material composed of this resin composition so that the surface on which the roughened plating layer was formed faced the sheet material side of the resin composition.

[0090] The metal substrate laminated as described above, the sheet material composed of the resin composition, and the metal plate were heated while being pressurized in the lamination direction, the resin composition was cured to form an insulating resin layer, and the metal substrate and the insulating resin layer were bonded to each other, and the insulating resin layer and the metal plate were bonded to each other, thereby obtaining an insulating circuit board. A pressurizing pressure in the lamination direction was 10 MPa, a heating temperature was 180°C, and a holding time at the heating temperature was 60 minutes.

20 [0091] The following items were evaluated for the obtained insulating circuit board as described above.

25 (Kurtosis and Root Mean Square Deviation)

[0092] The bonded interface between the circuit layer and the insulating resin layer was observed by using a laser microscope OLS5000 with an objective lens with a magnification of 100 times in a measurement range of 129 μm × 129 μm, the sample tilt and noise were removed, and a kurtosis of scale-limited surface Sku at the bonded interface and a root mean square deviation of scale-limited surface Sq at the bonded interface were calculated.

30 [0093] Next, a kurtosis of assessed profile Rku at the bonded interface and a root mean square deviation of scale-limited surface Rq at the bonded interface were calculated in the direction in which the roughness was considered to be the coarsest. At least three or more points were measured in the measurement range, and an average value thereof was described in Table.

(Overhang Rate)

40 [0094] The insulating circuit board was cut along the diagonal direction and along the lamination direction, and the cross-section of the bonded interface between the circuit layer and the insulating resin layer was observed to obtain a SIM image (512 pixels = 11 μm) at a magnification of 10,000 times. This SIM image was binarized by using image analysis software ImageJ, noise was manually removed, and an outline was then extracted.

45 [0095] The outline-extracted cross-sectional curvilinear coordinates were output in csv, and the number of overlapping metal regions in the Y direction was counted for a length of 512 pixels in the X direction. In addition, pixels extending in the Y direction (pixels adjacent to the Y direction) were excluded so that the vertical lines would not be counted in duplicate. Then, the number of overlapping regions on each position of an X-axis was divided by the total X-coordinate length to obtain an overhang rate.

50 [Overhang rate] = [Total number of overhang regions for each position of X-axis]/[Number of pixels in X direction] × 100 (%)

55 [0096] A measurement example is shown in Fig. 5. In the cross-sectional curve shown in Fig. 5, the number of overlapping regions in the Y direction for each position of the X-axis is 0, 1, 1, 0, 0, 0, 0, 0, 1, 1, 2, 2, 1, 1, 0, in order from the left, the total of these is 10, and the number of pixels in the X direction is 15. As a result, the overhang rate is 10/15 × 100, which is 67%.

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(Reflow Treatment After Moisture Absorption Treatment)

**[0097]** The above-mentioned insulating circuit board was placed in a constant temperature and humidity chamber (temperature of 85°C, humidity of 85%) and held for 3 days. Thereafter, the insulating circuit board was charged into a heating furnace and reflowed at 290°C for 10 minutes.

**[0098]** In the insulating circuit board after carrying out the reflow treatment, a bonding rate between the circuit layer and the insulating resin layer and a dielectric breakdown voltage were evaluated as follows.

(Bonding Rate)

**[0099]** The bonding rate between the circuit layer and the insulating resin layer was evaluated by using an ultrasonic flaw detector (FineSAT200 manufactured by Hitachi Power Solutions Co., Ltd.) and calculated from the following Equation. Here, an initial bonding area is an area to be bonded before bonding. Since the peeling is shown by the white part in the bonding part in the image obtained by binarizing ultrasonic-detected image, the area of this white part is defined as an exfoliation area.

$$\text{(Bonding rate)} = \{(\text{Initial bonding area}) - (\text{Exfoliation area})\} / (\text{Initial bonding area}) \times 100$$

(Dielectric Breakdown Voltage)

**[0100]** As shown in Fig. 6, the metal substrate 11 was placed on a base plate 61, a probe 62 was brought into contact with the circuit layer 13, and the partial discharge was evaluated. A partial discharge tester manufactured by MITSUBISHI CABLE INDUSTRIES, LTD. was used as a measuring device. A test atmosphere was Fluorinert (tm) FC-770 manufactured by 3M.

**[0101]** Then, a voltage was boosted by a step profile (holding time for 30 seconds) every 0.5 kV, and a voltage at which the dielectric breakdown occurred (the voltage at which the leakage current was 10 mA or higher) was defined as the dielectric breakdown voltage.

**[0102]** The evaluation results are shown in Table 1.

[Table 1]

		Bonded interface					Evaluation	
		Kurtosis		Overhang rate (%)	Root mean square deviation (μm)		Bonding rate (%)	Dielectric breakdown voltage (V)
		Rku	Sku		Rq	Sq		
Examples of the present embodiment	1	3.10	3.40	20.7	0.44	0.44	98	7.6
	2	3.50	3.50	16.7	0.37	0.35	97	7.0
	3	5.20	5.90	7.3	0.31	0.28	95	6.6
	4	3.10	2.80	10.5	0.38	0.43	88	7.7
	5	5.80	5.50	7.1	0.67	0.77	86	6.0
	6	3.60	3.30	7.3	0.20	0.23	85	7.4
	7	3.30	3.40	16.2	0.20	0.10	84	7.8
	8	4.50	5.00	13.3	0.88	0.90	98	5.8
Comparative example	1	2.70	2.50	18.4	0.67	0.69	80	7.5
	2	10.30	9.40	13.6	0.20	0.24	91	5.1
	3	3.40	3.20	4.2	0.30	0.26	82	7.8

**[0103]** In Comparative Example 1 in which the kurtosis of assessed profile Rku at the bonded interface of the circuit layer was 2.70 and the kurtosis of scale-limited surface Sku at the bonded interface of the circuit layer was 2.50, the bonding rate after the moisture absorption reflow was as low as 80%, and the adhesion between the circuit layer and the insulating resin layer was insufficient.

**[0104]** In Comparative Example 2 in which the kurtosis of assessed profile Rku at the bonded interface of the circuit layer was 10.30 and the kurtosis of scale-limited surface Sku at the bonded interface of the circuit layer was 9.40, the dielectric

breakdown voltage after the moisture absorption reflow was as low as 5.1 V, and the insulation properties was insufficient.

**[0105]** In Comparative Example 3 in which the overhang rate was 4.2%, the bonding rate after the moisture absorption reflow was as low as 82%, and the adhesion between the circuit layer and the insulating resin layer was insufficient.

5 **[0106]** On the other hand, in Examples 1 to 8 of the present invention, in which at least one of the kurtosis Rku of contour curve at the bonded interface of the circuit layer and the kurtosis Sku of contour surface at the bonded interface of the circuit layer was in the range of 2.75 or more and 6.00 or less, and the overhang rate is 7% or more, the bonding rate after the moisture absorption reflow was 84% or more, and the adhesion between the circuit layer and the insulating resin layer was excellent. In addition, the dielectric breakdown voltage after the moisture absorption reflow was 5.8 V or more, and the insulating resin layer was excellent in insulation properties. In each of Examples 1 to 8 of the present invention, at least one  
10 of the root mean square deviation Rq of contour curve at the bonded interface of the circuit layer and the root mean square deviation Sq of contour surface at the bonded interface of the circuit layer was in the range of 0.20 μm or more and 0.90 μm or less. In addition, in each of Examples 1 to 8 of the present invention, since both the kurtosis of assessed profile Rku at the bonded interface of the circuit layer and the kurtosis of scale-limited surface Sku at the bonded interface of the circuit layer were within the range of 2.75 or more and 6.00 or less, the adhesion between the circuit layer and the insulating resin layer  
15 was particularly excellent.

**[0107]** Furthermore, in each of Examples 1 to 6, and 8 of the present invention, in which both the root mean square deviation of assessed profile Rq at the bonded interface of the circuit layer and the root mean square deviation of scale-limited surface Sq at the bonded interface of the circuit layer were in the range of 0.20 μm or more and 0.90 μm or less, the bonding rate after the moisture absorption reflow was 85% or more, and the adhesion between the circuit layer and the insulating resin layer was particularly excellent.  
20

**[0108]** According to the examples of the present invention, from the above experimental results, it was confirmed that it was possible to provide the insulating circuit board (bonded body), in which the adhesion between the insulating resin layer (insulating resin member), the circuit layer (metal part) was excellent and the insulation properties in the insulating resin layer (insulating resin member) was excellent, and the insulating circuit board can be used stably.  
25

[Reference Signs List]

**[0109]**

- 30 10: Insulating circuit board (bonded body)  
11: Metal substrate (metal part)  
12: Insulating resin layer (insulating resin member)  
13: Circuit layer (metal part)  
18: Protrusion  
35 19: Recess

**Claims**

40 **1.** A bonded body having a structure in which an insulating resin member 12 made of  
an insulating resin and a metal 13 part made of a metal are bonded, wherein a bonded interface between the insulating resin member 12 and the metal part 13 has an uneven shape including a protrusion 18 in which the metal part 13 protrudes toward  
45 an insulating resin member side and a recess 19 in which the metal part 13 retracts from the insulating resin member side,

at least one of a kurtosis Rku of contour curve at the bonded interface of the metal part 13 and a kurtosis Sku of contour surface at the bonded interface of the metal part 13 is in a range of 2.75 or more and 6.00 or less, and an overhang rate that indicates a length ratio of regions overlapping in a lamination direction in a direction along the bonded interface is 7% or more.  
50

**2.** The bonded body according to Claim 1,  
wherein at least one of a root mean square deviation Rq of contour curve at the bonded interface of the metal part and a root mean square deviation Sq of contour surface at the bonded interface of the metal part is in a range of 0.20 μm or more and 0.90 μm or less.  
55

**3.** An insulating circuit board 10 comprising:

an insulating resin layer; 12 and  
 a circuit layer 13 in which a metal plate is bonded to one surface of the insulating resin layer,  
 wherein a bonded interface between the insulating resin layer and the circuit layer has an uneven shape including  
 a protrusion 18 in which the circuit layer protrudes toward an insulating resin layer side and a recess 19 in which  
 the circuit layer retracts from the insulating resin layer side,  
 at least one of a kurtosis  $R_{ku}$  of contour curve at the bonded interface of the circuit layer and a kurtosis  $S_{ku}$  of  
 contour surface at the bonded interface of the circuit layer is in a range of 2.75 or more and 6.00 or less, and  
 an overhang rate that indicates a length ratio of regions overlapping in a lamination direction in a direction along  
 the bonded interface is 7% or more.

4. The insulating circuit board according to Claim 3,  
 wherein at least one of a root mean square deviation  $R_q$  of contour curve at the bonded interface of the circuit layer and  
 a root mean square deviation  $S_q$  of contour surface at the bonded interface of the circuit layer is in a range of 0.20  $\mu\text{m}$  or  
 more and 0.90  $\mu\text{m}$  or less.

**Patentansprüche**

1. Verbundener Körper, der eine Struktur aufweist, in der ein isolierendes Harzelement 12, das aus einem isolierende Harz und einem Metallteil 13 hergestellt ist, das aus einem Metall hergestellt ist, verbunden sind,

wobei eine verbundene Schnittstelle zwischen dem isolierenden Harzelement 12 und dem Metallteil 13 eine unregelmäßige Form aufweist, die einen Vorsprung 18 einschließt, in den der Metallteil 13 zu einer Seite des isolierenden Harzelements hin vorsteht, und eine Aussparung 19, in der sich der Metallteil 13 von der Seite des isolierende Harzelements zurückzieht,  
 mindestens eines eines Häufigkeitsgrads  $R_{ku}$  von Kontourkurve an der verbundenen Schnittstelle des Metallteils 13 und Häufigkeitsgrads  $S_{ku}$  von Kontouroberfläche an der verbundenen Schnittstelle des Metallteils 13 in einem Bereich von 2,75 oder mehr und 6,00 oder weniger liegt, und  
 eine Überhangrate, die ein Längenverhältnis von Regionen angibt, die in eine Laminierungsrichtung überlappen, in einer Richtung entlang der verbundenen Schnittstelle 7 % oder mehr ist.

2. Verbundener Körper nach Anspruch 1,  
 wobei mindestens eines einer mittleren quadratischen Abweichung  $R_q$  von Kontourkurve an der verbundenen Schnittstelle des Metallteils und mittleren quadratischen Abweichung  $S_q$  von Kontouroberfläche an der verbundene Schnittstelle des Metallteils in einem Bereich von 0,20  $\mu\text{m}$  oder mehr und 0,90  $\mu\text{m}$  oder weniger liegt.

3. Isolierende Leiterplatte 10, umfassend:

eine isolierende Harzschiicht 12 und  
 eine Leitungsschiicht 13, in der eine Metallplatte mit einer Oberfläche der isolierenden Harzschiicht verbunden ist,  
 wobei eine verbundene Schnittstelle zwischen der isolierenden Harzschiicht und der Leitungsschiicht eine unregelmäßige Form aufweist, die einen Vorsprung 18 aufweist, in den die Leitungsschiicht zu einer Seite der isolierenden Harzschiicht hin vorsteht, und eine Aussparung 19, in der sich die Leitungsschiicht von der Seite der isolierenden Harzschiicht zurückzieht,  
 mindestens eines eines Häufigkeitsgrads  $R_{ku}$  von Kontourkurve an der verbundenen Schnittstelle der Leiterschicht und Häufigkeitsgrads  $S_{ku}$  von Kontouroberfläche an der verbundenen Schnittstelle der Leiterschicht in einem Bereich von 2,75 oder mehr und 6,00 oder weniger liegt, und  
 eine Überhangrate, die ein Längenverhältnis von Regionen angibt, die in eine Laminierungsrichtung überlappen, in einer Richtung entlang der verbundenen Schnittstelle 7 % oder mehr ist.

4. Isolierende Leiterplatte nach Anspruch 3,  
 wobei mindestens eines einer mittleren quadratischen Abweichung  $R_q$  von Kontourkurve an der verbundenen Schnittstelle der Leiterschicht und einer mittleren quadratischen Abweichung  $S_q$  von Kontouroberfläche an der verbundene Schnittstelle der Leiterschicht in einem Bereich von 0,20  $\mu\text{m}$  oder mehr und 0,90  $\mu\text{m}$  oder weniger liegt.

**Revendications**

1. Corps lié ayant une structure dans laquelle sont liés un élément 12 de résine isolante constitué d'une résine isolante et un élément 13 métallique constitué d'un métal,

5 dans lequel une interface liée entre l'élément 12 en résine isolante et l'élément 13 métallique présente une forme irrégulière incluant une saillie 18 dans laquelle l'élément 13 métallique fait saillie vers un côté d'élément en résine isolante et un évidement 19 dans lequel l'élément 13 métallique se rétracte du côté d'élément en résine isolante, au moins l'une d'une courbe de contour Rku de kurtosis au niveau de l'interface liée de l'élément 13 métallique et d'une surface de contour Sku de kurtosis au niveau de l'interface liée de l'élément 13 métallique est dans une plage de 2,75 ou plus et de 6,00 ou moins, et un taux de dépassement qui indique un rapport de longueur de régions se chevauchant dans une direction de stratification dans une direction le long de l'interface liée est de 7 % ou plus.

- 15 2. Corps lié selon la revendication 1, dans lequel au moins l'un d'un écart quadratique moyen Rq de la courbe de contour au niveau de l'interface liée de l'élément métallique et un écart quadratique moyen Sq de la surface de contour au niveau de l'interface liée de l'élément métallique est dans une plage de 0,20  $\mu\text{m}$  ou plus et de 0,90  $\mu\text{m}$  ou moins.

- 20 3. Carte 10 de circuit imprimé d'isolation comprenant :

une couche 12 de résine isolante ; et  
une couche 13 de circuit dans laquelle une plaque métallique est liée à une surface de la couche de résine isolante,  
25 dans laquelle une interface liée entre la couche de résine isolante et la couche de circuit présente une forme irrégulière incluant une saillie 18 dans laquelle la couche de circuit fait saillie vers un côté de couche de résine isolante et un évidement 19 dans lequel la couche de circuit se rétracte du côté de couche de résine isolante, au moins l'une d'une courbe de contour Rku de kurtosis au niveau de l'interface liée de la couche de circuit et d'une surface de contour Sku de kurtosis au niveau de l'interface liée de la couche de circuit est dans une plage de 2,75 ou plus et de 6,00 ou moins, et un taux de dépassement qui indique un rapport de longueur de régions se chevauchant dans une direction de stratification dans une direction le long de l'interface liée est de 7 % ou plus.

- 35 4. Carte de circuit imprimé d'isolation selon la revendication 3, dans laquelle au moins l'un d'un écart quadratique moyen Rq de la courbe de contour au niveau de l'interface liée de la couche de circuit et un écart quadratique moyen Sq de la surface de contour au niveau de l'interface liée de la couche de circuit est dans une plage de 0,20  $\mu\text{m}$  ou plus et de 0,90  $\mu\text{m}$  ou moins.

40

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FIG. 1

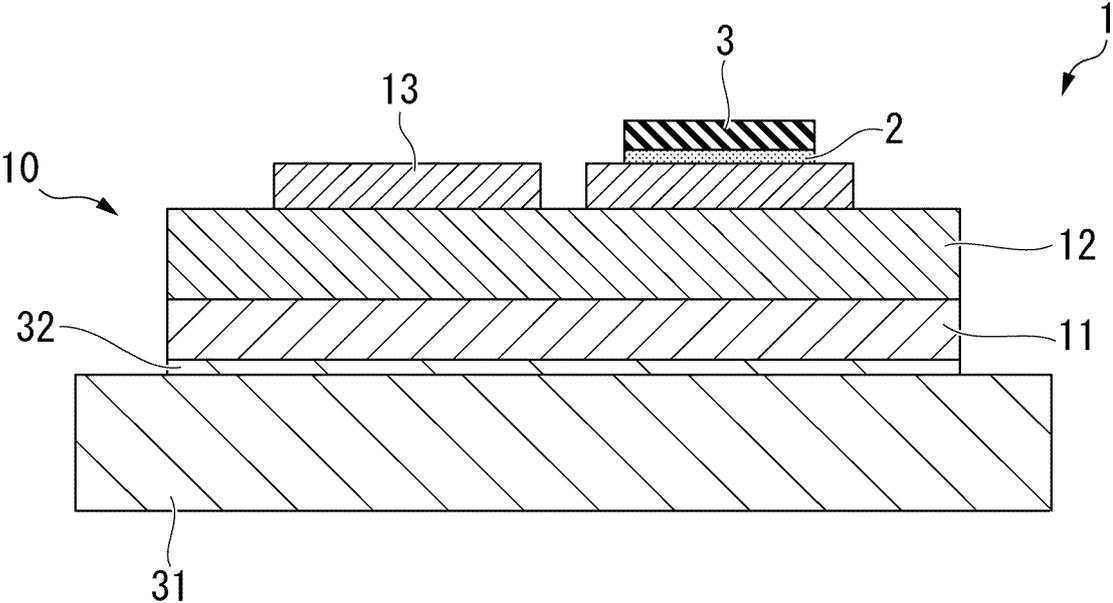


FIG. 2

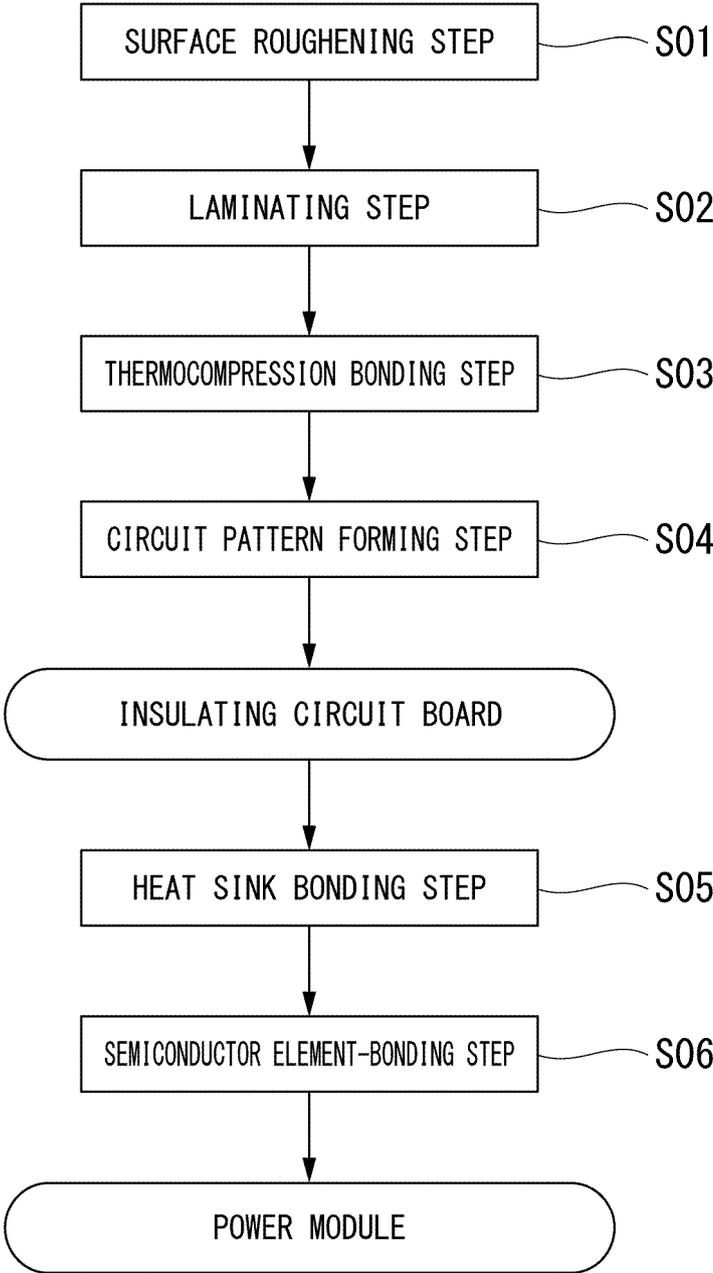


FIG. 3

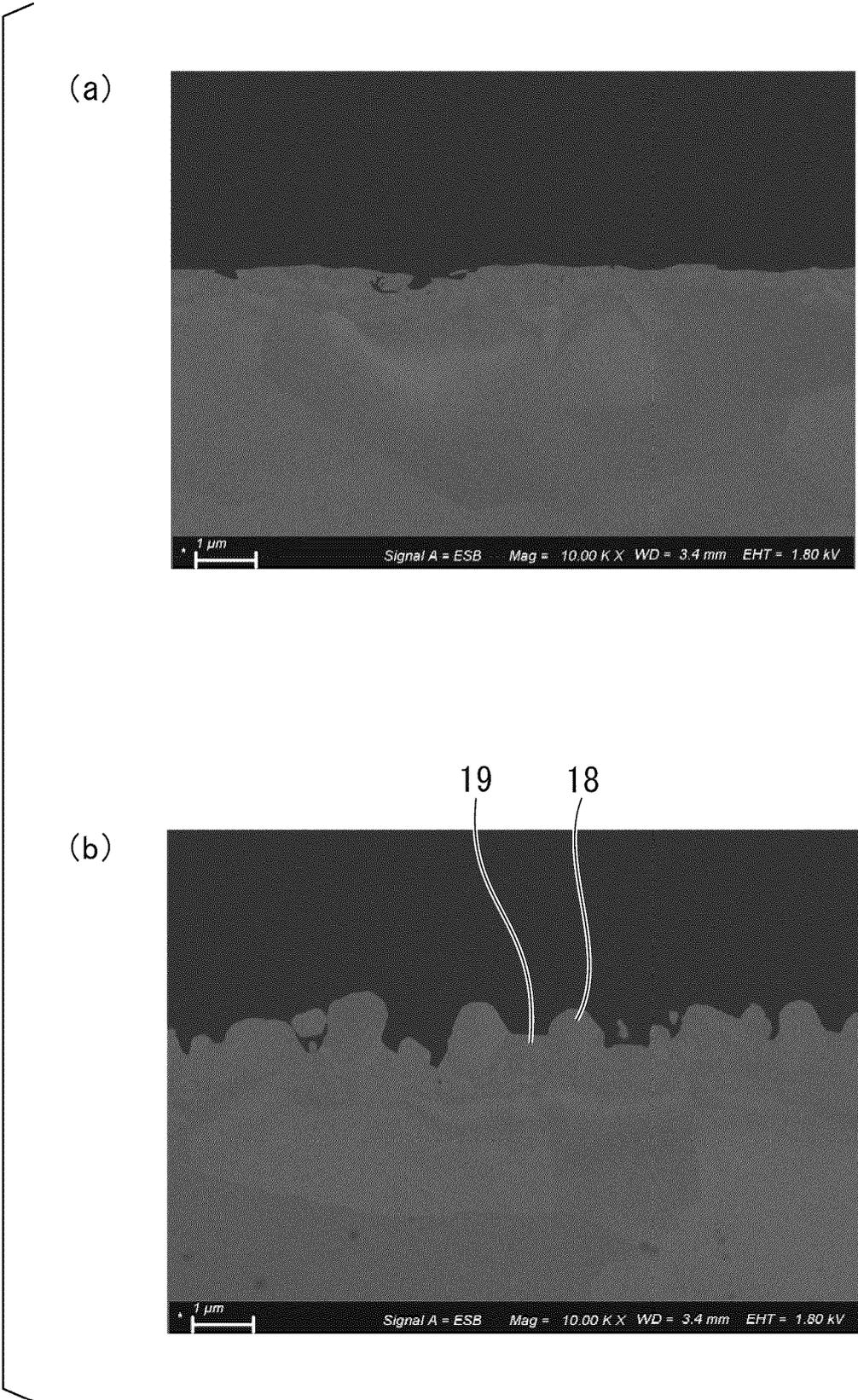


FIG. 4

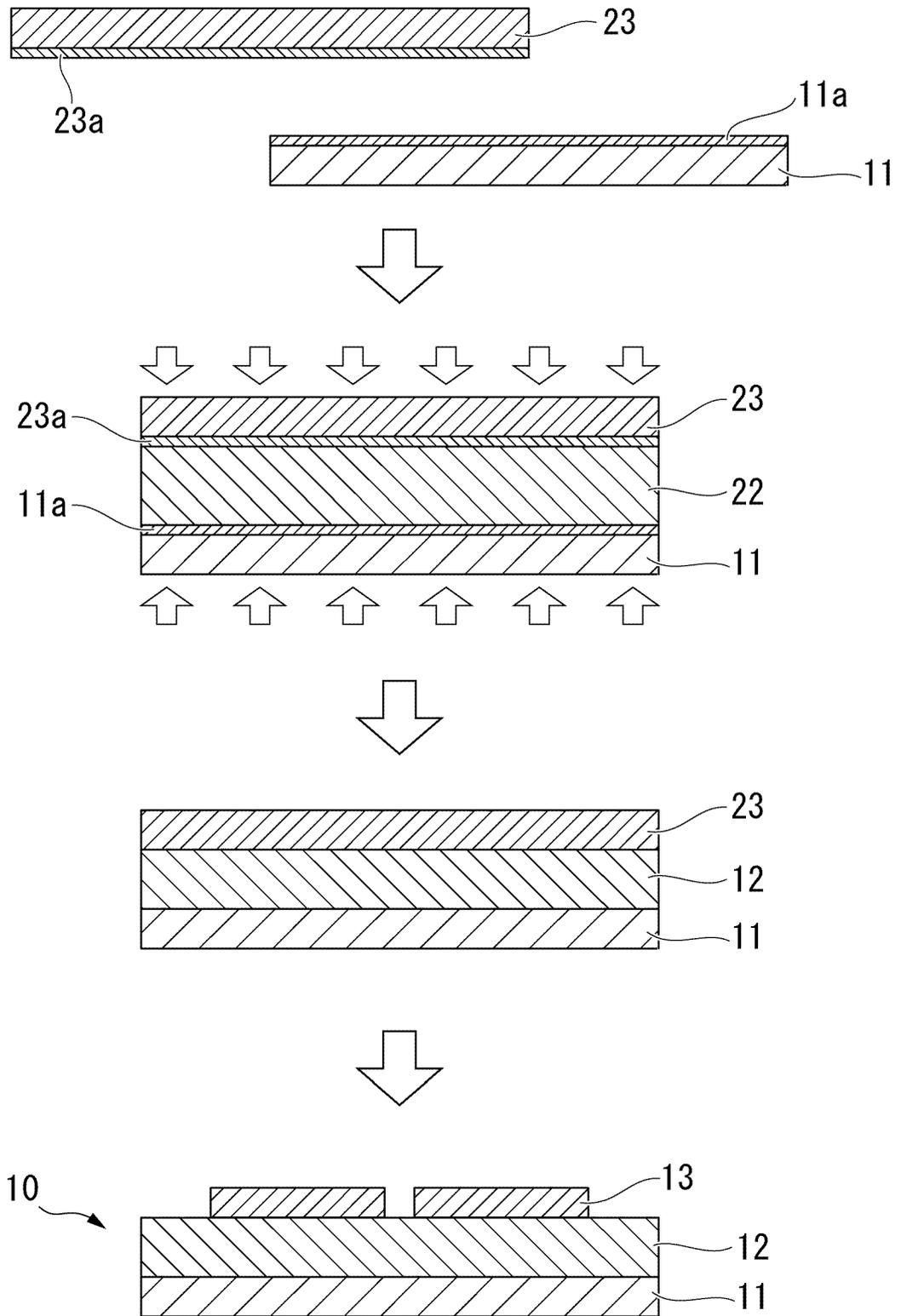
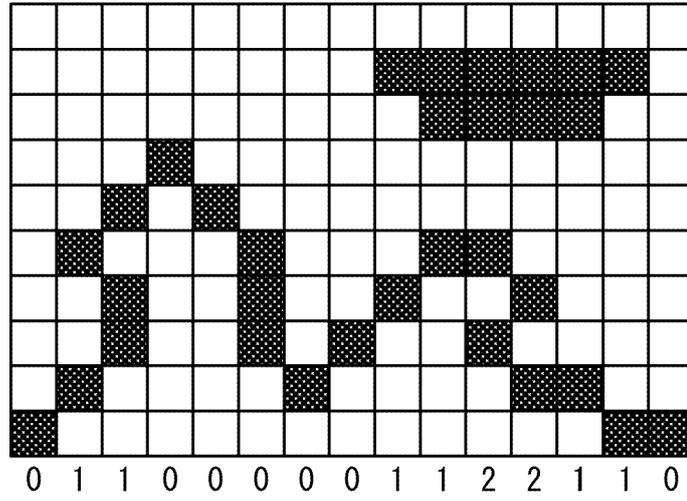


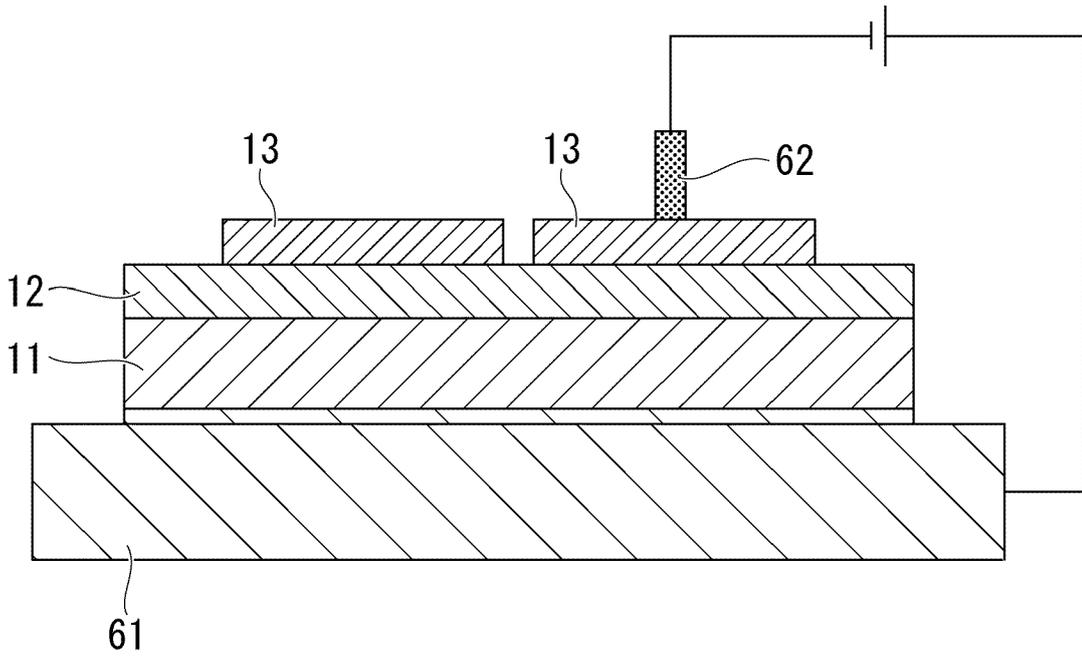
FIG. 5



$$0+1+1+0+0+0+0+0+1+1+2+2+1+1+0 = 10$$

$$\text{OVERHANG RATE} = 10/15 \times 100 = 67\%$$

FIG. 6



**REFERENCES CITED IN THE DESCRIPTION**

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